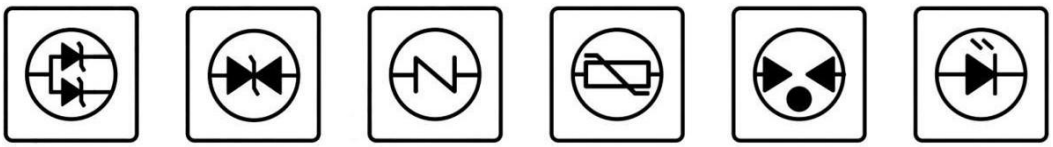
MSKSEMI 美森科
SEMICONDUCTOR



SI2309CDS-T1-MS

Product specification

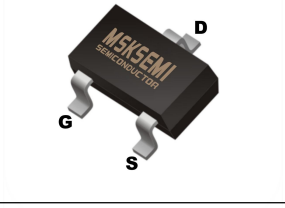
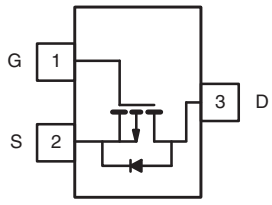
General Features

- V_{DS} =-60V,I_D =-2A
- $R_{DS(ON)}$ <160mΩ @ V_{GS}=-10V
- $R_{DS(ON)}$ <200mΩ @ V_{GS}=-4.5V

Application

- Load switch
- PWM application

Reference News

PACKAGE OUTLINE	PIN Configuration	Marking
 SOT-23		N9ADE

Absolute Maximum Ratings T_C=25℃unlessotherwise noted

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage	-60	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current-Continuous	-2	A
I_{DM}	Drain Current-Pulsed (Note 1)	-8	A
P_D	Maximum Power Dissipation	1.5	W
T_J,T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	℃
$R_{\theta JA}$	Thermal Resistance,Junction-to-Ambient (Note 2)	83.3	℃/W

Electrical Characteristics (T_C=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=-250μA	-60	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-60V,V_{GS}=0V	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=-250μA	-1.4	-2.0	-2.6	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=-10V, I_D=-1.5A	-	140	160	mΩ
		V_{GS}=-4.5V, I_D=-1.5A	-	160	200	mΩ
Forward Transconductance	g_{FS}	V_{DS}=-5V,I_D=-1.5A	-	3	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=-30V,V_{GS}=0V, F=1.0MHz	-	444.2	-	PF
Output Capacitance	C_{oss}		-	19.6	-	PF
Reverse Transfer Capacitance	C_{rss}		-	17.9	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=-30V, I_D=-1.5A, V_{GS}=-10V,R_G=3Ω	-	40	-	nS
Turn-on Rise Time	t_r		-	35	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	15	-	nS
Turn-Off Fall Time	t_f		-	10	-	nS
Total Gate Charge	Q_g	V_{DS}=-30,I_D=-1.5A, V_{GS}=-10V	-	11.3	-	nC
Gate-Source Charge	Q_{gs}		-	2.7	-	nC
Gate-Drain Charge	Q_{gd}		-	1.6	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=-1.5A	-		-1.2	V
Diode Forward Current (Note 2)	I_S		-	-	-1.6	A
Reverse Recovery Time	t_{rr}	T_J = 25°C, I_F =- 1.5A di/dt = -100A/μs(Note3)	-	25		nS
Reverse Recovery Charge	Qrr		-	31		nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics (Curves)

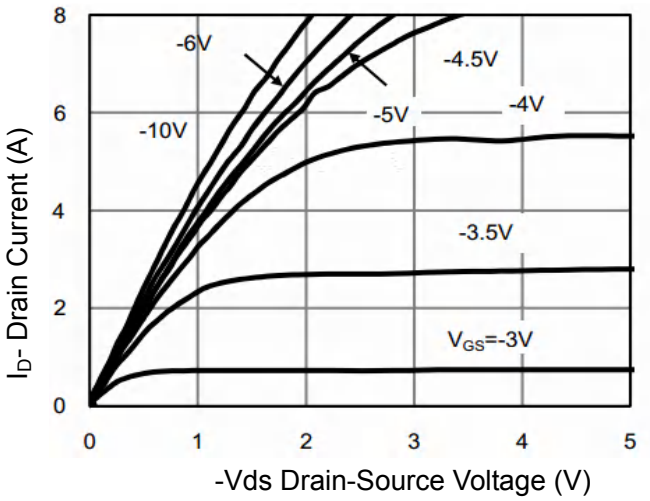


Figure 1 Output Characteristics

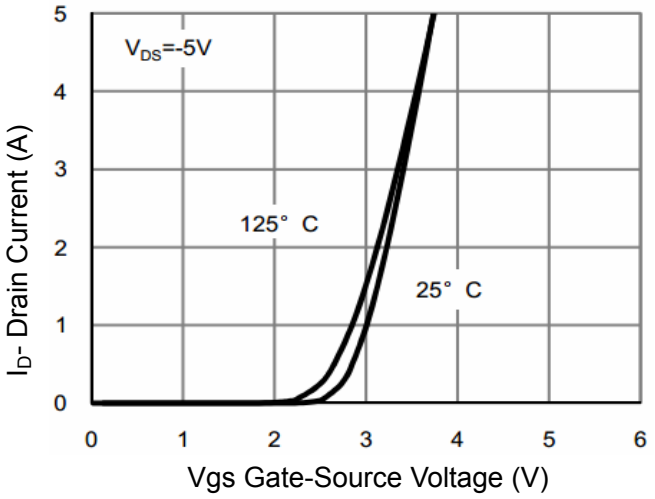


Figure 2 Transfer Characteristics

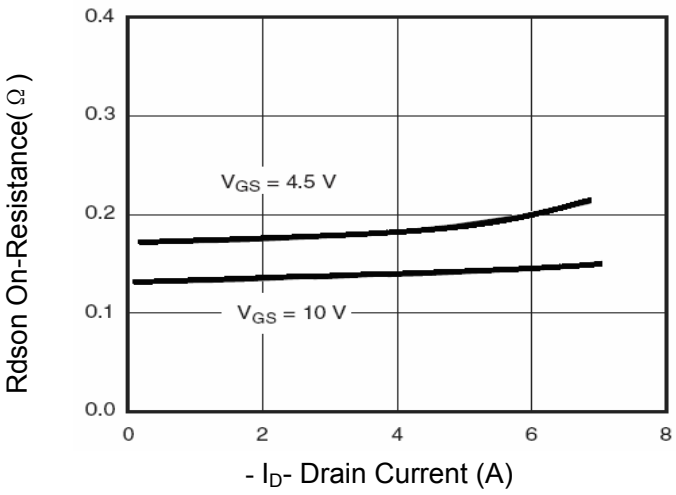


Figure 3 Rdson- Drain Current

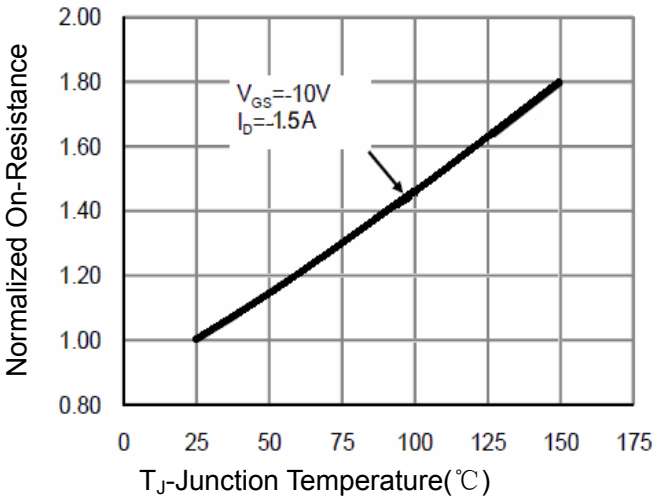


Figure 4 Rdson-Junction Temperature

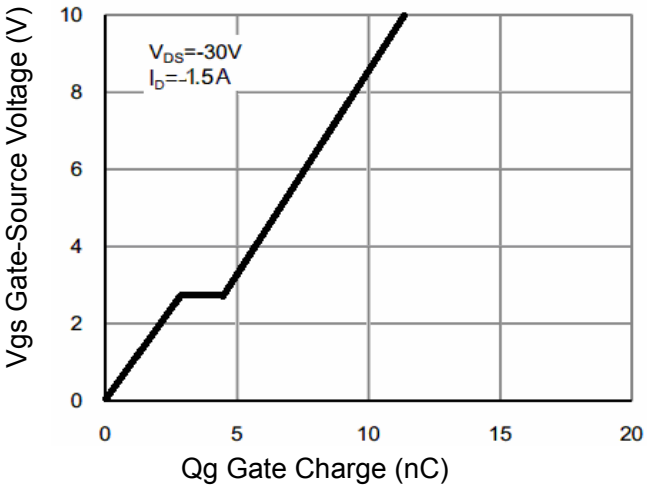


Figure 5 Gate Charge

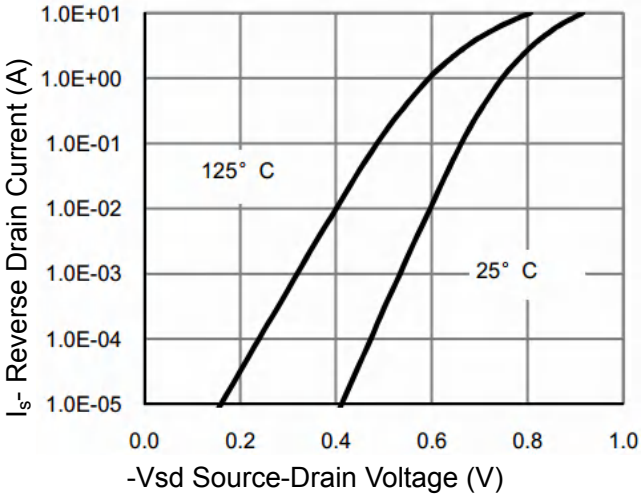


Figure 6 Source- Drain Diode Forward

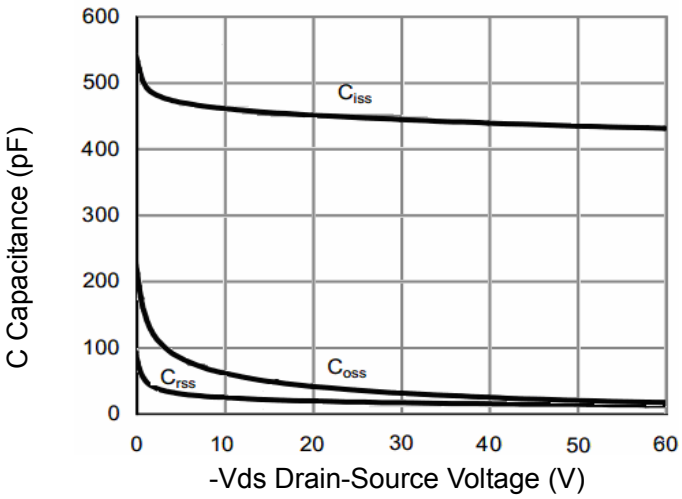


Figure 7 Capacitance vs Vds

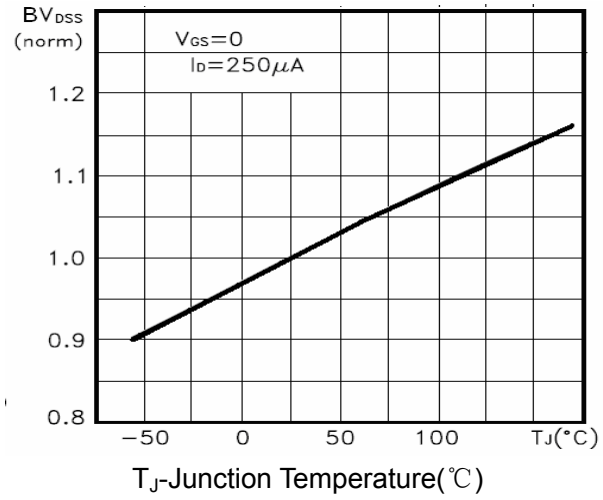


Figure 9 BV_{DSS} vs Junction Temperature

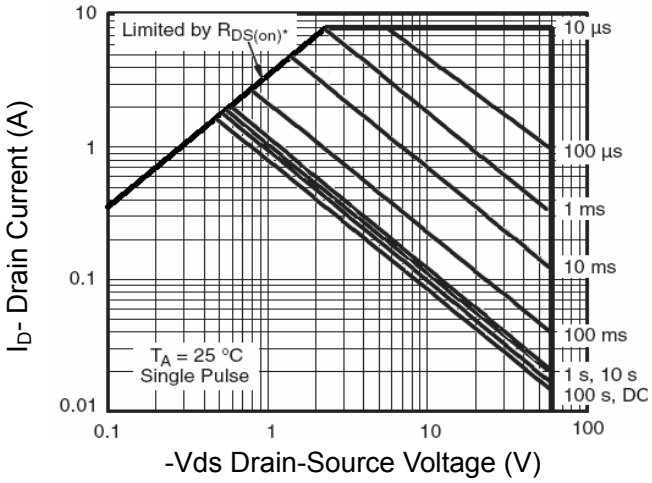


Figure 8 Safe Operation Area

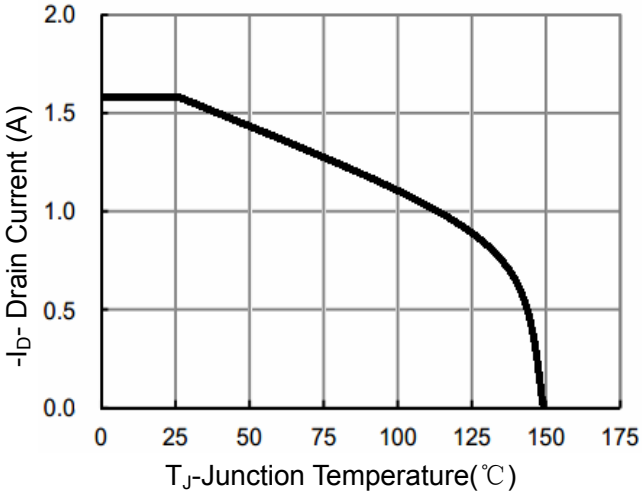


Figure 10 ID Current De-rating

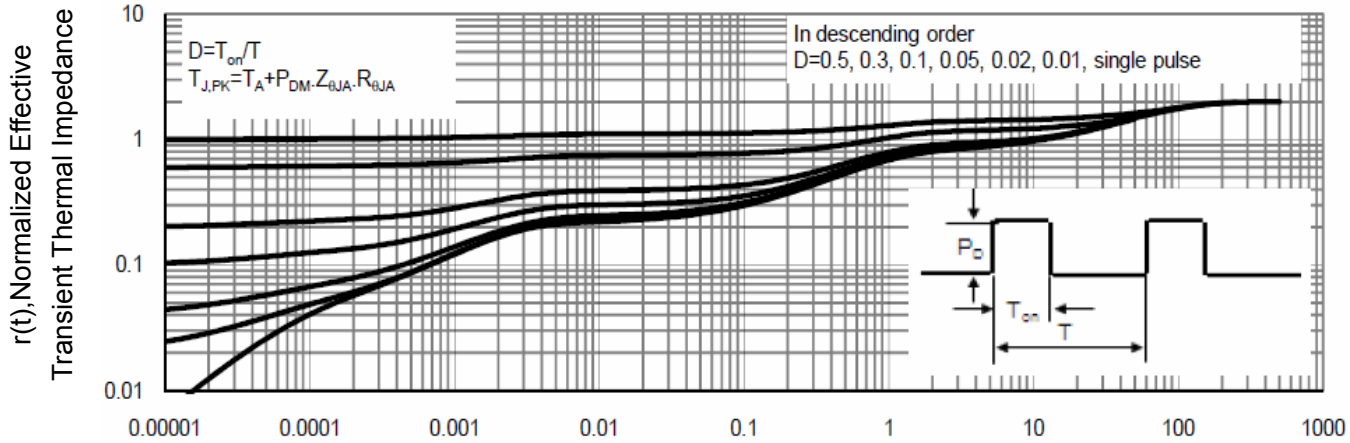
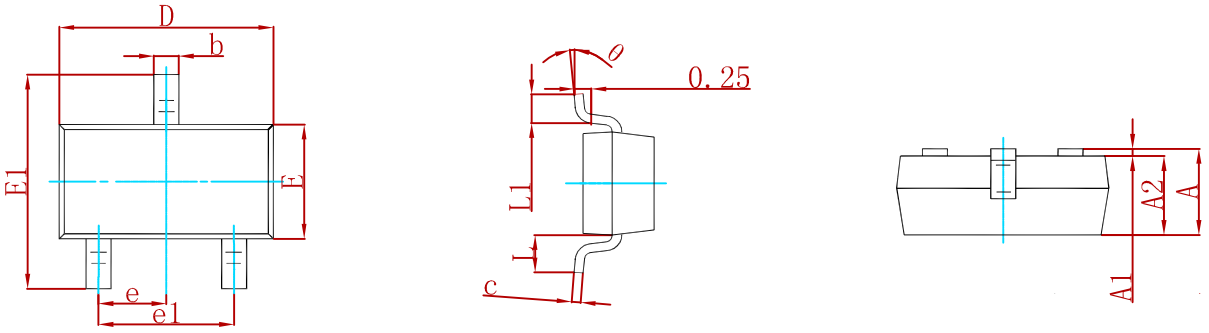


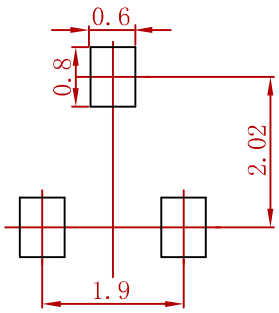
Figure 11 Normalized Maximum Transient Thermal Impedance

PACKAGE MECHANICAL DATA



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
SI2309CDS-T1-MS	SOT-23	3000

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